

Photoemission (I) Spectroscopy

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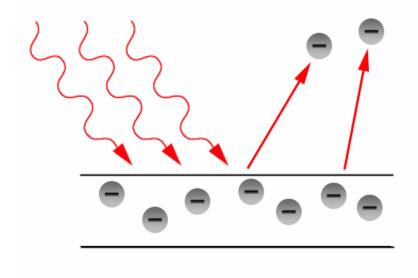
Outline

- 1. What is photoemission spectroscopy?
- 2. Fundamental aspects of photoemission.
- 3. Examples.
- 4. Increase bulk sensitivity: HAXPES.
- 5. Challenging future directions.

General reference books:

- 1. "Photoelectron Spectroscopy" 3rd Ed. by S. Hufner, Springer-Verlag 2003
- 2. "Angle-Resolved Photoemission: Theory and Current Applications", S. D. Kevan, ed., Amsterdam; Elsevier 1992

What is photoemission?



Photon in -> electron out (emission)

What are the samples and probed states?

Atoms atomic orbitals (states)

Molecules molecular orbitals

core level states (atomic like)

Nanoprticles valence bands/states

core level states (atomic like)

Solids valence bands

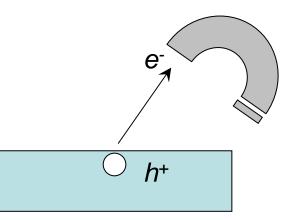
core level states (atomic like)

What is photoemission spectroscopy? (photoelectron spectroscopy) (PES)

hv Monochromatized photons

sample

Electron energy analyzer



Initial state: ground (neutral) state

Final state: hole (excited) state

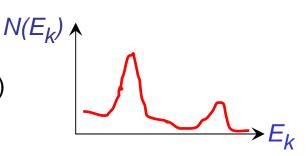
Conservation of energy

 $E_k = hv + E_i - E_f$ (most general expression)

 E_{k} : photoelectron kinetic energy

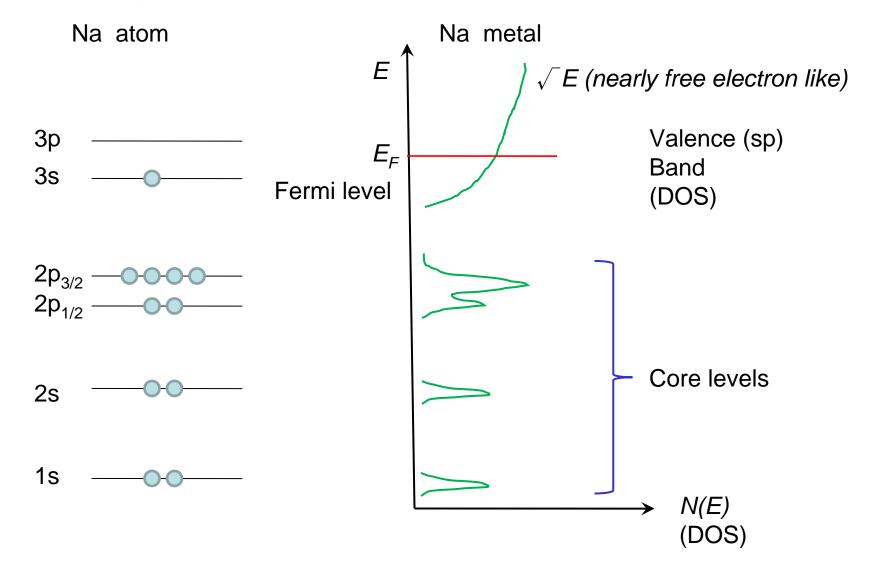
 $E_i(N)$: total initial state system energy

 $E_f(N-1)$: total final state system energy

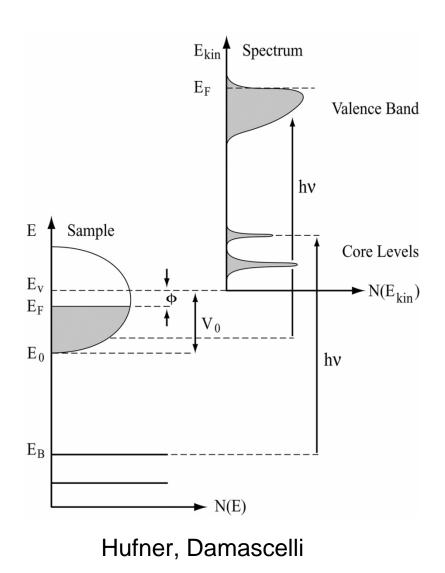


Energy Distribution Curve (EDC) (Spectrum)

Single particle description of energy levels (Density of States) (most convenient in PE)



Energetics in PES



$$E_k = hv - E_B - \phi$$

Conservation of energy

 E_{v} : vacuum (energy) level

E_F: Fermi (energy) level

 $\phi = E_v - E_F$: work function

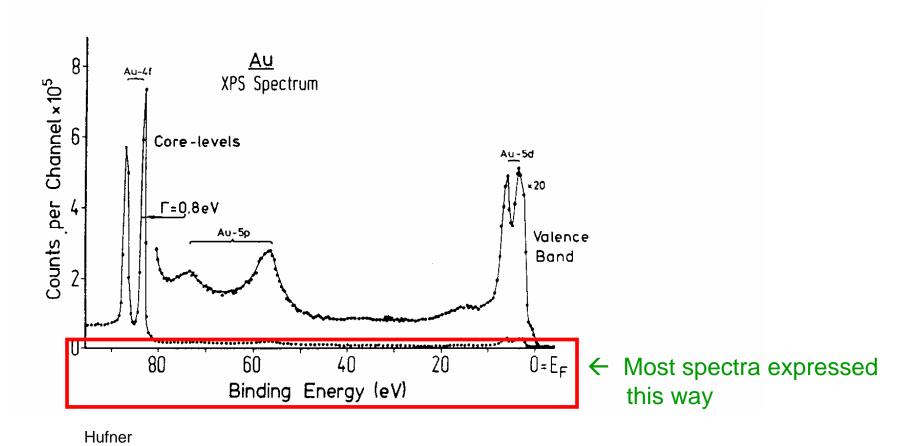
 E_0 : bottom of valence band

 $V_0 = E_v - E_o$: inner potential

 E_k^{max} marks E_F in spectra E_B measured relative to $E_F = 0$

Usually fixed photon energy scanning not needed

An XPS Energy Distribution Curve (EDC)



Light sources and terminology

Ultraviolet Photoemission Spectroscopy (UPS)

UV He lamp (21.2 eV, 40.8 eV) valence band PE, direct electronic state info

X-ray Photoemission Spectroscopy (XPS)

(Electron Spectroscopy for Chemical Analysis) (ESCA)

x-ray gun (Al: 1486.6 eV, Mg: 1253.6 eV) core level PE, indirect electronic state info chemical analysis

Synchrotron radiation:

continuous tunable wavelength valence band: <100 eV, maybe up to several keV core level: 80-1000 eV, maybe up to several keV depending on core level binding energies

Inelastic Electron Mean Free Path (IMFP)

 $I(d) = I_o e^{-d/\lambda(E)}$

 $\lambda(E)$: IMFP depending on kinetic energy relative to E_{r}

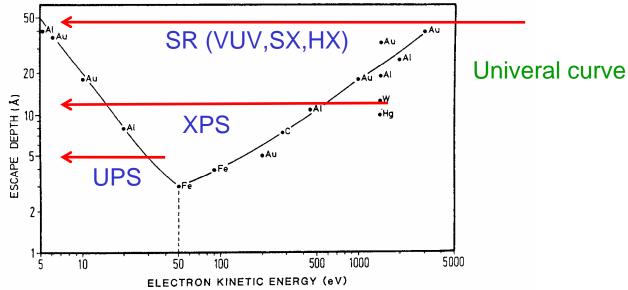


Fig.1.9. Electron escape depth as a function of their kinetic energy for various metals. The data indicate a universal curve with a minimum of $2 \div 5$ Å for kinetic energies of $50 \div 100$ eV. The scatter of the data is evident from the values obtained at $E_{kin} = 1480$ eV

Hufner

Minimum due to electron-electron scattering, mainly plasmons

PE is a surface sensitive technique! (requires UHV)

High energy photoemission: several keV to increase bulk sensitivity

Table 1-1. Electron binding energies, in electron volts, for the elements in their natural forms.

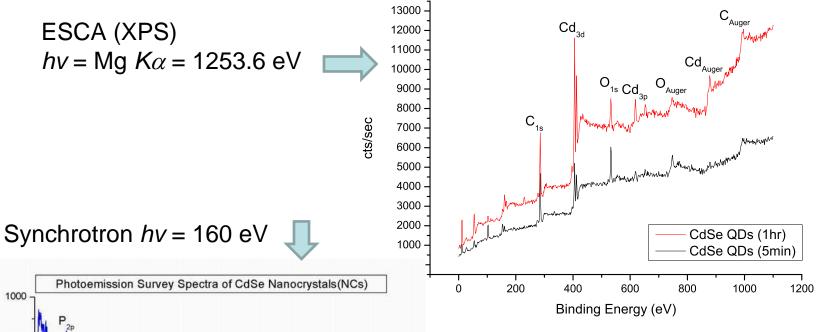
Element	K 1s	L ₁ 2s	L ₂ 2p _{1/2}	L ₃ 2p _{3/2}	M ₁ 3s	M ₂ 3p _{1/2}	M ₃ 3p _{3/2}	M ₄ 3d _{3/2}	$M_5 \ 3d_{5/2}$	N ₁ 4s	$N_2 \ 4p_{1/2}$	N ₃ 4p _{3/2}
1 H	13.6										•	
2 He	24.6*											
3 Li	54.7*								-(:)	ore	Ie.	/el b
4 Be	111.5*											
5 B	188*											
6 C	284.2*								Cr	nara	7Ct6	eris [,]
7 N	409.9*	37.3*							OI.	ı aı c	<i>x</i> 000	
8 O	543.1*	41.6*									_ _	
9 F	696.7*								- 62	acn	ele	eme
10 Ne	870.2*	48.5*	21.7*	21.6*								,,,,
11 Na	1070.8†	63.5†	30.65	30.81								
12 Mg	1303.0†	88.7	49.78	49.50								
13 Al	1559.6	117.8	72.95	72.55								
14 Si	1839	149.7*b	99.82	99.42							- 14 10	
15 P	2145.5	189*	136*	135*						nae	er n	rint
16 S	2472	230.9	163.6*	162.5*						3	- P	
17 CI	2822.4	270*	202*	200*								
18 Ar	3205.9*	326.3*	250.6†	248.4*	29.3*	15.9*	15.7*					
19 K	3608.4*	378.6*	297.3*	294.6*	34.8*	18.3*	18.3*					
20 Ca	4038.5*	438.4†	349.7†	346.2†	44.3 †	25.4†	25.4†			.	Las	
23 V	5465	626.7†	519.8†	512.1†	66.3†	37.2†	37.2†		((ore	1e\	/el [
24 Cr	5989	696.0†	583.8†	574.1†	74.1†	42.2†	42.2†			•••		
25 Mn	6539	769.1†	649.9†	638.7†	82.3†	47.2†	47.2†		ما م			
26 Fe	7112	844.6†	719.9†	706.8†	91.3†	52.7†	52.7†		Dr	1010	on (ene
27 Co	7709	925.1†	793.2†	778.1†	101.0†	58.9†	59.9†		Γ.	. • • •		• • • •
28 Ni	8333	1008.6†	870.0†	852.7†	110.8†	68.0†	66.2†					
29 Cu	8979	1096.7†	952.3†	932.7	122.5†	77.3†	75.1†					
30 Zn	9659	1196.2*	1044.9*	1021.8*	139.8*	91.4*	88.6*	10.2*	10.1*			
31 Ga	10367	1299.0*b	1143.2†	1116.4†	159.5†	103.5†	100.0†	18.7†	18.7†			
32 Ge	11103	1414.6*b	1248.1*b	1217.0*b	180.1*	124.9*	120.8*	29.8	29.2			
33 As	11867	1527.0*b	1359.1*b	1323.6*b	204.7*	146.2*	141.2*	41.7*	41.7*			
34 Se	12658	1652.0*b	1474.3*b	1433.9*b	229.6*	166.5*	160.7*	55.5*	54.6*			
35 Br	13474	1782*	1596*	1550*	257*	189*	182*	70*	69*			
36 Kr	14326	1921	1730.9*	1678.4*	292.8*	222.2*	214.4	95.0*	93.8*	27.5*	14.1*	14.1*
37 Rb	15200	2065	1864	1804	326.7*	248.7*	239.1*	113.0*	112*	30.5*	16.3*	15.3 *
38 Sr	16105	2216	2007	1940	358.7†	280.3†	270.0†	136.0	134.2†	38.9	21.3	20.1†
39 Y	17038	2373	2156	2080	392.0*b	310.6*	298.8*	157.7†	155.8†	43.8*	24.4*	23.1*
40 Zr	17998	2532	2307	2223	430.3†	343.5†	329.8†	181.1†	178.8†	50.6†	28.5†	27.1†
41 Nb	18986	2698	2465	2371	466.6†	376.1†	360.6†	205.0†	202.3†	56.4†	32.6†	30.8†
42 Mo	20000	2866	2625	2520	506.3†	411.6†	394.0†	231.1†	227.9†	63.2†	37.6†	35.5†
43 Tc	21044	3043	2793	2677	544*	447.6	417.7	257.6	253.9*	69.5*	42.3*	39.9*
44 Ru	22117	3224	2967	2838	586.1*	483.5†	461.4†	284.2†	280.0†	75.0	46.3†	43.2†
45 Rh	23220	3412	3146	3004	628.1†	521.3†	496.5†	311.9†	307.2†	81.4*b	50.5†	47.3†
46 Pd	24350	3604	3330	3173	671.6†	559.9†	532.3†	340.5†	335.2†	87.1*b	55.7†a	50.9†
47 Ag	25514	3806	3524	3351	719.0†	603.8†	573.0†	374.0†	368.3	97.0*	63.7†	58.3†

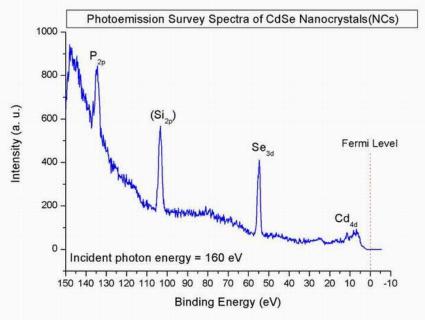
binding energies are stic of each orbital of ent

ts

BE independent of ergy used

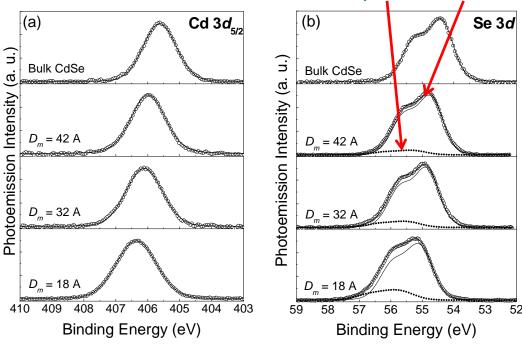
Core level photoemission: chemical analysis of elements





Different photon energy →
different relative cross section
for various core levels →
Relative intensity changes
with photon energy

surface component bulk component



Surface core level shift (chemical and/or environmental)

A case study of IMFP applied to PE of CdSe nano particles with tunable SR How to choose photon energies for valence and different core levels with the max surface sensitivity?

Bulk CdSe $D_m = 42 \text{ A}$ $D_m = 18 \text{ A}$ $D_m = 18 \text{ A}$ 10 8 6 4 2 0 -2

Binding Energy (eV)

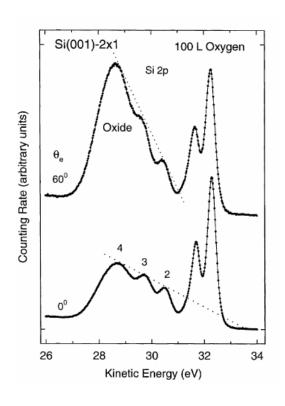
Actual choices:

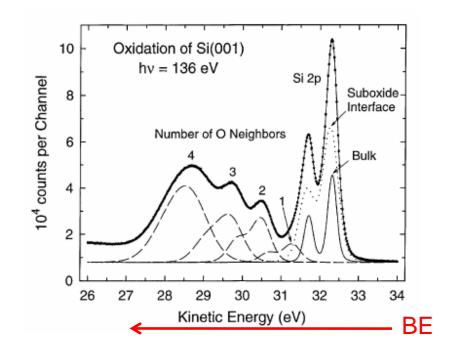
 $Cd \ 3d_{5/2}$: 480 eV Se 3d: 120 eV Valence band: 50 eV

 $E_k \sim 45\text{-}74 \text{ eV}$, most surface sensitive Wu, PRB 2007 NSRRC

Core level photoemission: chemical shift

higher oxidation state => higher BE





higher emission angle

→ more surface sensitive

(IMFP) Pi, SS 2001 NSRRC

Auger Electron Spectroscopy

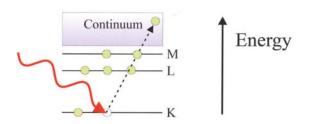
Core electron ionized by photons or high energy electrons
Non-radiative core hole decay
→ Auger electron emission
Radiative decay

→ Fluorescent x-ray emission

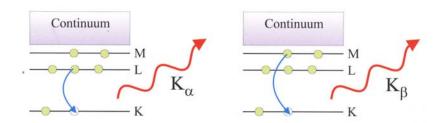
Comparison between PES and AES

PES: constant BE, Ek shift with changing photon energy AES: constant Ek, apparent BE shift with changing photon energy (synchrotron)

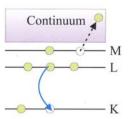
(a) Photoelectric absorption



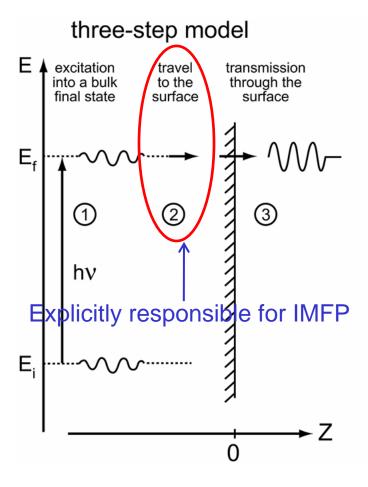
(b) Fluorescent X-ray emission



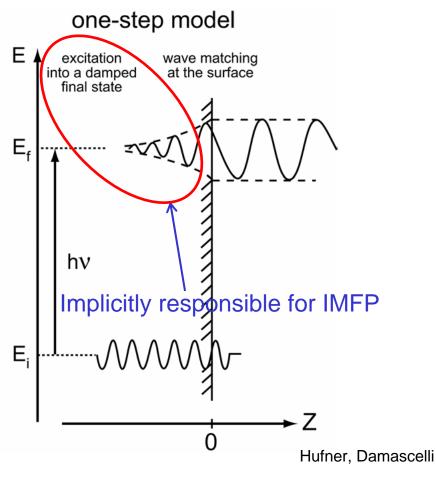
(c) Auger electron emission



Photoemission Process

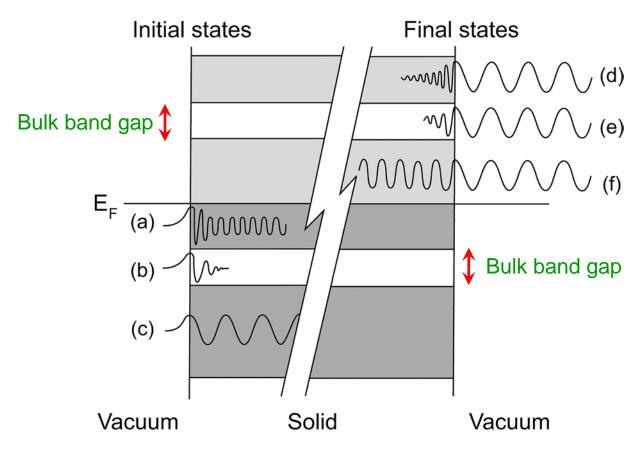






Rigorous, requires sophisticated calculation

Schematic wave functions of initial and final states (valence band initial states)

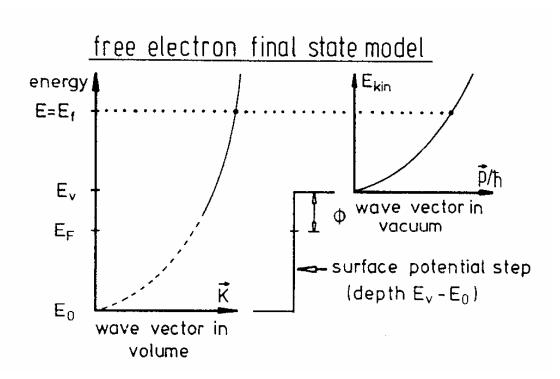


- (a) Surface resonance
- (b) Surface state
- (c) Bulk Bloch state

- (d) Surface resonance
- (e) in-gap evanescent state
- (f) Bulk Bloch final state

Electron kinetic energy inside and outside of solids

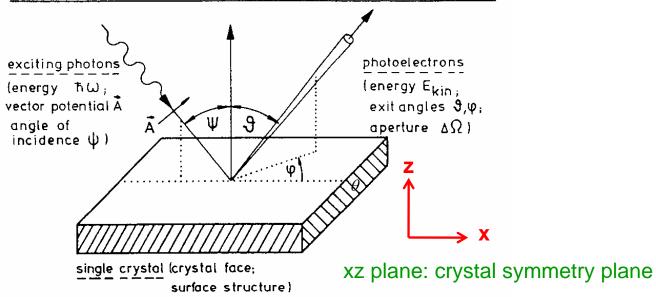
Inner potential: $E_V - E_0$



Concept of inner potential is used to deduce 3D band structure from PE data assuming free electron like final state inside solids

Angle Resolved Photoemission Spectroscopy (ARPES)

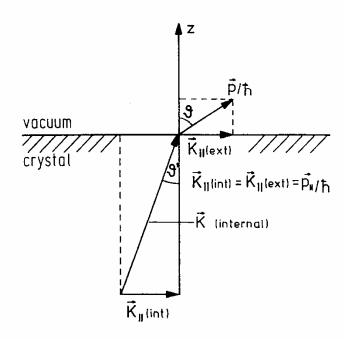
Angular Resolved Photoemission Spectroscopy(ARPES)



Electron emission angle: Θ

Photon incident angle: ϕ , s- and p-polarization

Conservation of linear momentum parallel to the surface



$$k = \sqrt{\frac{2m}{\hbar^2}} E_k \cdot \sin \theta$$

$$k_{\parallel (\text{lint})} = k_{\parallel (\text{ext})} = \hat{p}_{\text{u}/h}$$
 $k_{\parallel (\text{ext})} = \hat{p}_{\text{u}/h}$ $k_{\parallel (\text{ext})} = \hat{p}_{\text{u}/h}$

 k_{\parallel} (inside) = k_{\parallel} (outside)

Conservation of liner momentum

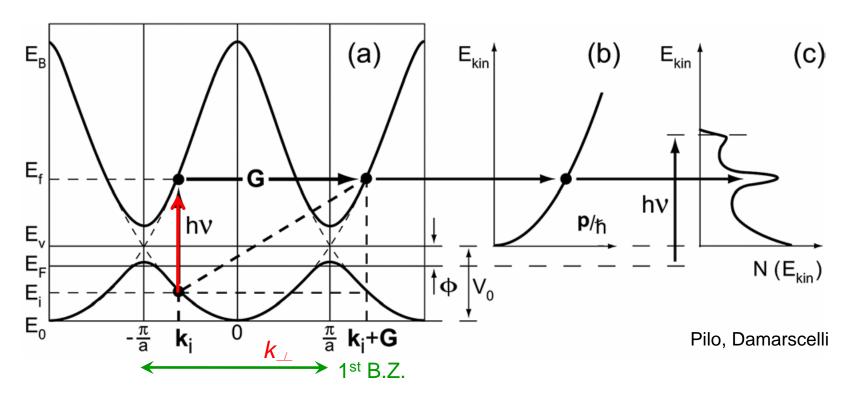
Important for 3D and 2D band mapping

 k_{\perp} (inside) $\neq k_{\perp}$ (outside) because of inner potential

Ultimately to deduce band dispersion $E(k_{\perp})$ or $E(k_{\perp}, k_{\parallel})$

Normal emission: $\theta = 0$, or $k_{||} = 0$, most used detection geometry

Band Mapping (3D) $E(k_{\perp}, k_{\parallel}=0)$



Vertical transition (using visible, uv and soft x-rays) at normal emission

For hard x-ray photon momentum cannot be neglected

Using different hv at normal emission to map out $E(k_{\perp})$

Bulk band structure and Fermi surfaces

Fermi surfaces:

Electron pockets and hole pockets
Related to
Hall coefficient
Electric conductivity
Magnetic susceptibility

(nearly free electron like) sp-band

Small dispersion *d*-band more localized state

Large dispersion *sp*-band extended state

Dispersion of a band can tell how localized or extended a state is in a solid

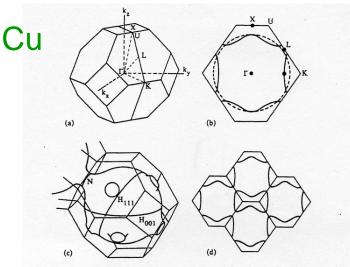


Fig. 10-15 Various aspects of the Fermi surface of Cu. (a) The Brillouin zone of an fcc lattice with some special points labeled. (b) A (110) section of the Brillouin zone. See the text for the meaning of the internal curves. (c) The proposed Fermi surface of Cu. (d) The extended zone picture of a (110) section of the Fermi surface showing the dog bone orbits.

Gap below $E_F(=0)$ at L-point

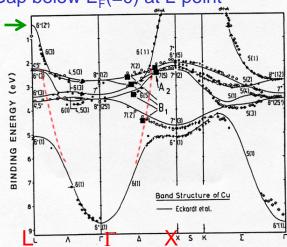
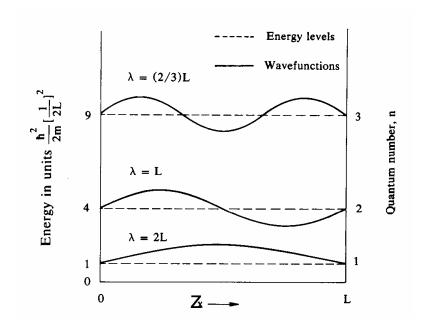


Fig.7.17. Occupied part of the band structure of Cu[7.39] with data points from various sources and a theoretical result [7.53]. Also shown (squares) are the two A_2 points and the four B_1 points from Fig.7.16

$$(111) \leftarrow \rightarrow (001)$$
 Hufner

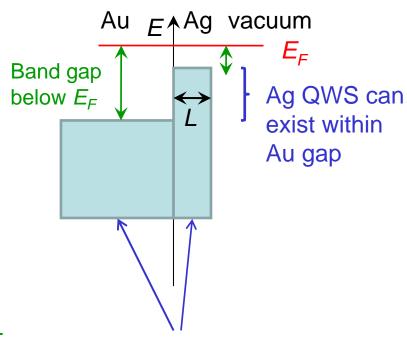
Quantum well states: manifestation of particle in a box in real materials



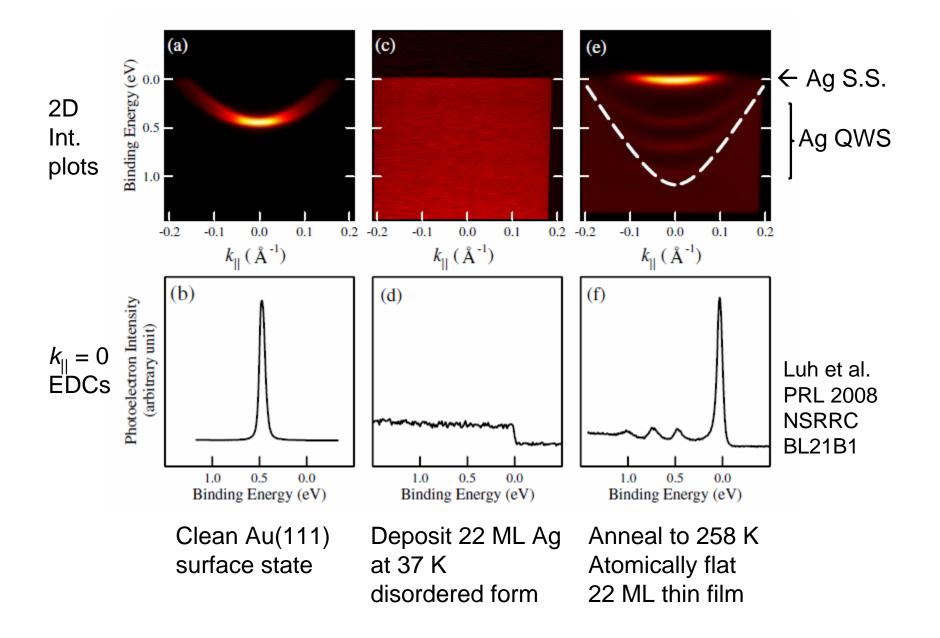
Quantized discretely along z-direction Energy levels depend on film thickness L

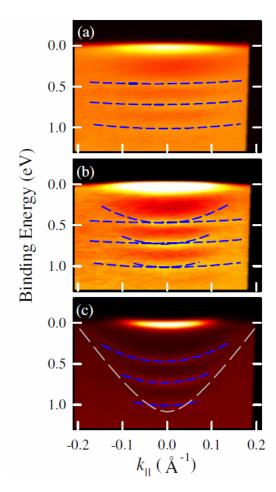
Nearly free electron like in xy-plane

Ag(111) thin films expitaxially grown on Au(111) substrate



Bulk projected bands along Γ L of Au and Ag, respectively

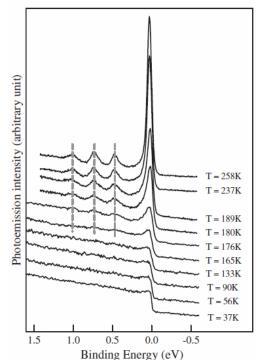




Anneal to 180 K QWS appear minimal flat dispersion Small localized domains within xy-plane

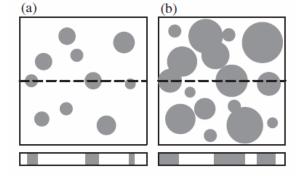
Anneal to 189 K Coexistence of two kinds of dispersion

Anneal to 258 K
Well developed
dispersion
Large, good
crystalline
0.2 domains
in xy-plane



Same QWS energies →
Same crystalline film
thickness along z
even though lateral
crystalline domains
grow from small to
large

Proposed growth model



Annealing Temp ———

One-particle spectral function near E_F measured by ARPES with many-particle correction (quasi-particle)

$$A(k,\omega) = -\frac{1}{\pi} \frac{\Sigma''(k,\omega)}{\left[\omega - \varepsilon_k - \Sigma'(k,\omega)\right]^2 + \left[\Sigma''(k,\omega)\right]^2}$$

 \mathcal{E}_k : single particle energy without many-particle correction $\omega = 0$: E_F

Self energy correction due to interaction with phonons, plasmons and electrons, etc.

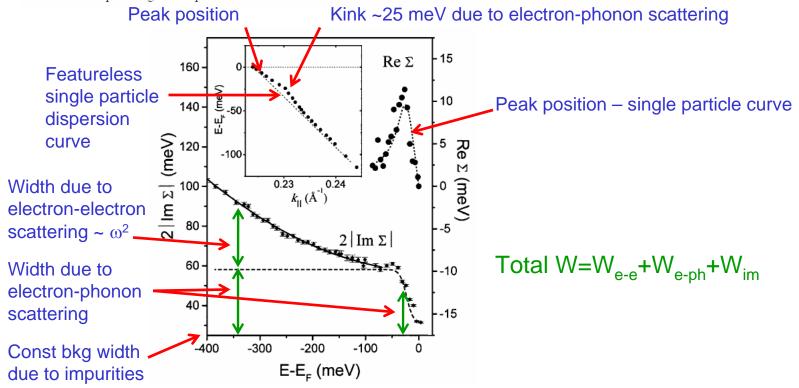
$$\Sigma(k,\omega) = \Sigma'(k,\omega) + i\Sigma''(k,\omega)$$

Real part: shift observed peak energy from single particle energy Imaginary part: peak FWHM = 2Σ "

Many-Body Effects in Angle-Resolved Photoemission: Quasiparticle Energy and Lifetime of a Mo(110) Surface State

T. Valla, A. V. Fedorov, P. D. Johnson, and S. L. Hulbert Department of Physics, Brookhaven National Laboratory, Upton, New York 11973-5000 National Synchrotron Light Source, Brookhaven National Laboratory, Upton, New York 11973-5000 (Received 28 January 1999)

In a high-resolution photoemission study of a Mo(110) surface state various contributions to the measured width and energy of the quasiparticle peak are investigated. Electron-phonon coupling, electron-electron interactions, and scattering from defects are all identified mechanisms responsible for the finite lifetime of a valence photohole. The electron-phonon induced mass enhancement and rapid change of the photohole lifetime near the Fermi level are observed for the first time.



Photoemission cross section in single particle approximation (1st step in 3-step model, inside bulk)

$$\begin{split} \frac{d\sigma}{d\Omega} &\propto \sum \left| \left\langle \Psi_f \middle| A \cdot p \middle| \Psi_i \right\rangle \right|^2 \cdot \delta \Big(E_f - E_i - h \, \nu \Big) \\ M_{fi} &= \left\langle \Psi_f \middle| A(r) \cdot p \middle| \Psi_i \right\rangle \cong A(0) \cdot \left\langle \Psi_f \middle| p \middle| \Psi_i \right\rangle \propto A(0) \cdot \left\langle \Psi_f \middle| r \middle| \Psi_i \right\rangle \\ & \text{dipole approximation} \end{split}$$

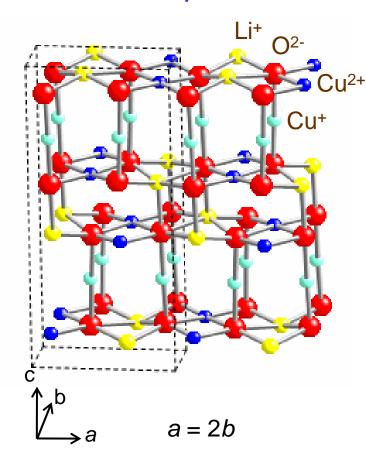
A: polarization vector

 Ψ_i : initial state (orbital) wave function (1s, 2p, valence states etc.) contain orbital symmetry information

 Ψ_f : final state (orbital) wave function ~ $\exp(i \mathbf{k} \cdot \mathbf{r})$ for high kinetic energy photoelectrons, no orbital symmetry retains (non-resonance photoemission) (orbital symmetry in final state is important in near edge absorption measurements (XAS) and in intermediate state in resonance photoemission) Dipole transition rule: $\Delta l = +1$

Symmetry selection rule for initial (valence) state governed by matrix element e.g. suppose A(0) = Ax, $\langle e^{ikz} | x | \psi_i(x) \rangle = 0$ if $\psi_i(-x) = +\psi_i(x)$ Important for crystalline samples

Symmetry of states in ARPES determined by selection rule example: LiCu2O2



Cu²⁺O²⁻₂ chains along b-axis built by edge sharing Cu²⁺O²⁻₄ plaquettes

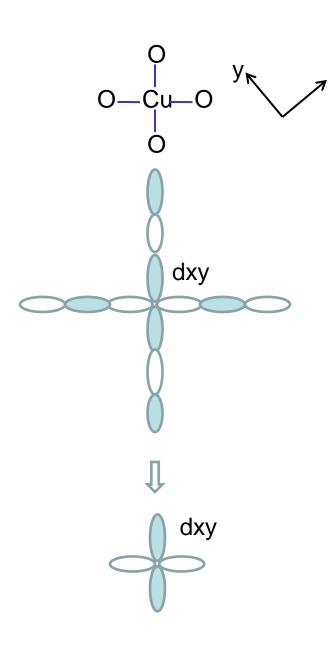
 $Cu^{2+}: 3d^9 \rightarrow spin-1/2$

Quasi-1D spin-1/2 chain

Coexistence of spin-spiral long range order with ferroelectricity → multiferronic

Ideal spin-1/2 1D chain system will have spin-charge separation of photo-hole decay Does it happen on LiCu2O2? Must be checked by ARPES (not discussed further)

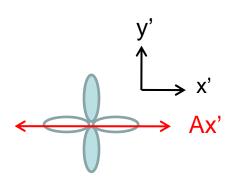
Will focus on symmetry of states determined by ARPES with polarization



Basic building unit: CuO4 planar plaquette

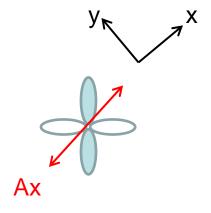
Highest energy state: Cu 3dxy and O 2p antibonding (AB) state

Still keeps dxy symmetry



Normal emission $|f\rangle = \exp(ikz)$ even to all symmetry op [i> even to y'z-plane, Ax' odd to y'z-plane < f|Ax'|i> = <+|-|+> = 0, forbidden

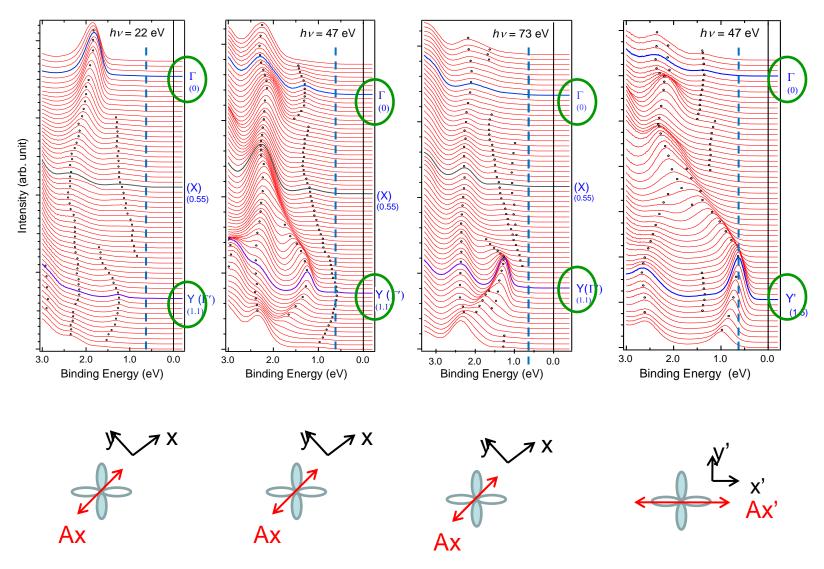
Off-normal emission [f> = $\exp(ikz+kx')$ even to x'z-plane |i> even to x'z-plane, Ax' even to x'z-plane <f| Ax' |i> = <+| + | +> != 0, allowed



Normal emission [f> = exp(ikz) even to all symmetry op [i> odd to xz-plane, Ax even to xz-plane <f| Ax |i> = <+| + |-> = 0, forbidden

Off-normal emission $|f> = \exp(ikz+ikx)$ even to xz-plane |i> odd to xz-plane, Ax even to xz-plane < f|Ax|i> = <+|+|-> = 0, forbidden

Focus on B.E. = 0.7 eV peak at Y'



The highest energy peak at 0.7 eV has dxy symmetry!

ARPES for valence band PE uses primarily VUV light because

- 1. Better absolute photon energy resolution for most BLs designed as const $\Delta E/E$.
- 2. Better photoionization cross section at low photon energy.
- 3. Better momentum resolution for a given angular resolution. $\Delta k|| = 0.5123 \sqrt{(Ek)} \cos(\theta) \Delta \theta$

SX ARPES has been tried for increasing bulk sensitivity, more free electron like final states and reduced matrix element effects. The increasing bulk sensitivity will be discussed.

NSRRC U9 BL21B1 BL and high resolution photoemission end station

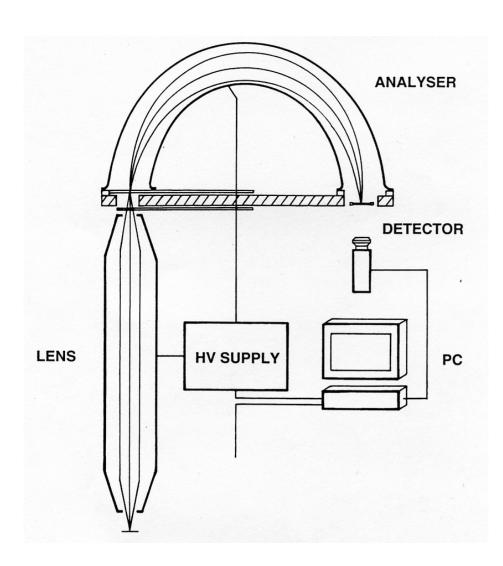


U9 undulator

CGM

Scienta SES 200 analyzer

Hemispherical electron energy analyzer



R1: radius of inner sphere

R2: radius of outer sphere

Ro=(R1+R2)/2 : mean radius

and along electron path

V1: inner potential

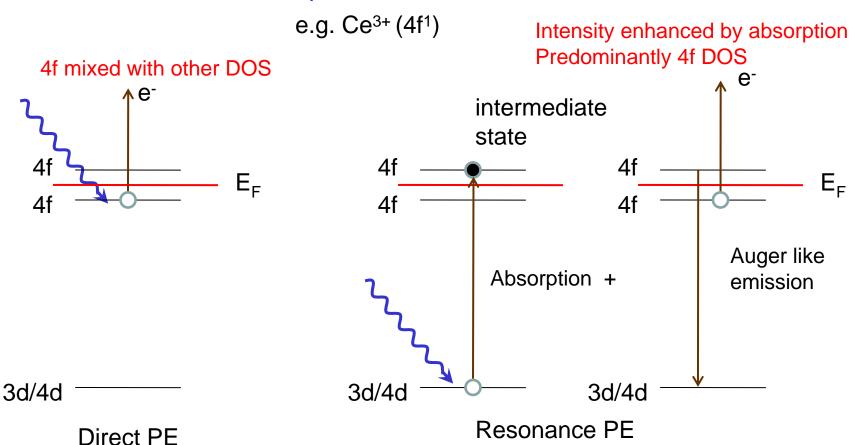
V2: outer potential

Ep: pass energy = electron

kinetic energy along mean

radius

Resonance photoemission (near-edge absorption followed by Auger like electron emission)



Comments on photoelectron IMFP

Valence band PE using VUV and SX has IMFP near minimum, very surface sensitive. It is great to probe surface electronic structure such as surface states and surface resonances.

Many strongly correlated systems have electronic structure sensitive to coordination, thus surface contains different electronic structure from that of deeper bulk. Great surface sensitivity posts a serious problem to probe true bulk properties.

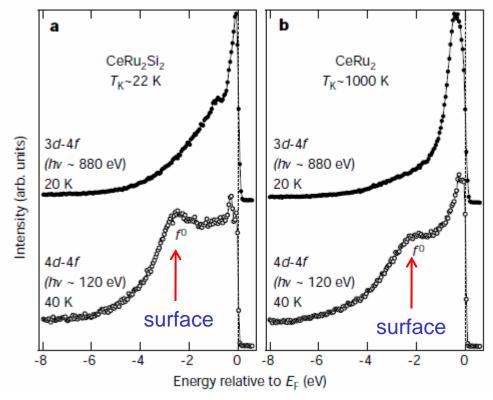
Need larger IMFP by using higher energy photons to enhance bulk sensitivity.

letters to nature

2000

Probing bulk states of correlated electron systems by high-resolution resonance photoemission

A. Sekiyama*, T. Iwasaki*, K. Matsuda*, Y. Saitoh†, Y. Ônuki‡ & S. Suga*



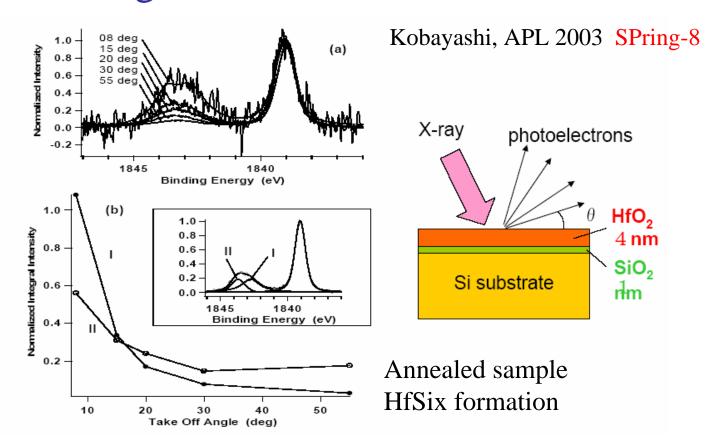
By using Ce 3d \rightarrow 4f Res. PE near 880 eV surface 4f component becomes greatly reduced compared to 4d \rightarrow 4f Res. PE near 120 eV, the resulting spectra are closer to true bulk 4f DOS.

Drive to go to even higher photon energies into hard x-ray regime

HArd X-ray PhotoEmission Spectroscopy (HAXPES)

HAXPES not only reach even closer to true bulk properties of strongly correlated systems, but also becomes capable of probing interface electronic structure, Very difficult using conventional VUV/SX.

HAXPES example: Hard x-ray photoemission on Si-high k insulator buried interface

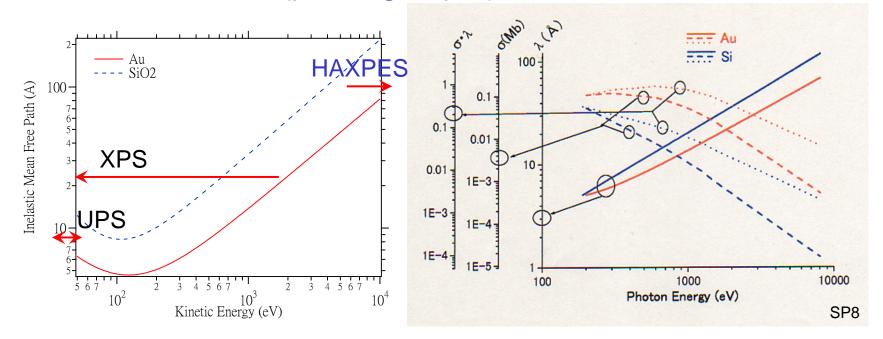


hv = 6 keV, $\Delta E \sim 0.24$ eV Take-off angle dependence => non-destructive depth profile Can probe buried interface at 35 nm! (achievable only by hard x-ray PE)

NSRRC HAXPES project at SPring-8

Why Hard X-rays?

Electron IMFP (probing depth) and Cross section

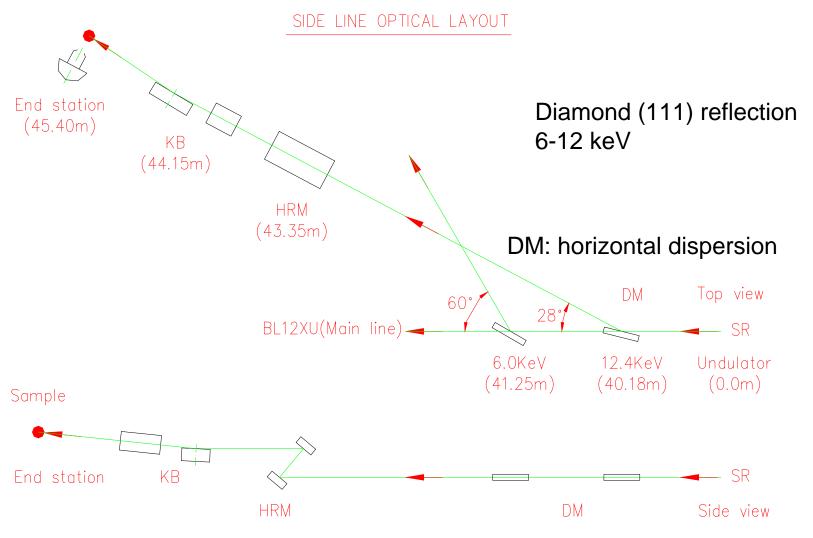


Higher Ek for deeper probing depth or more bulk sensitivity, for strongly correlated systems and interface properties

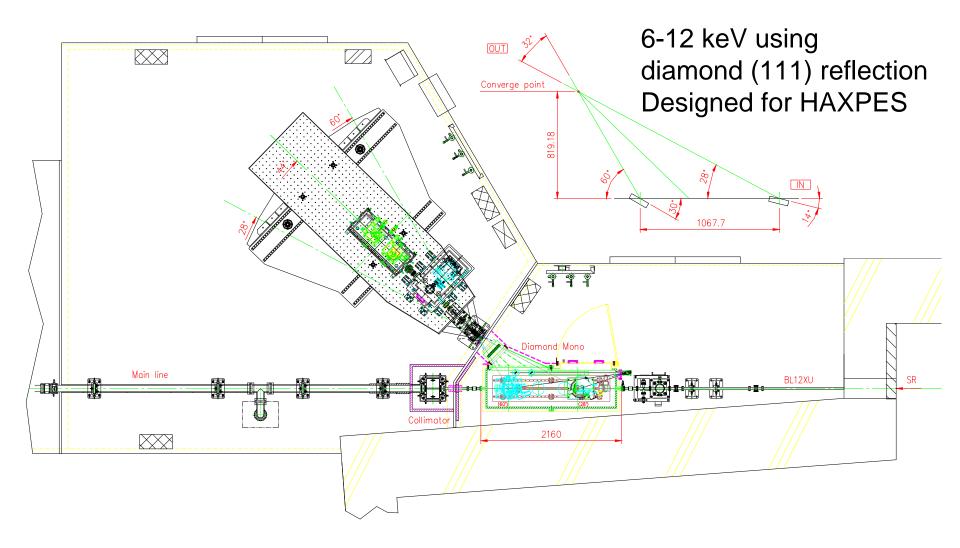
Photoemission signal $(\sigma \cdot \lambda)$ decreases rapidly > 1 keV Need photon source of higher flux/brightness (modern SR), efficient BL design and good electron analyzers

HAXPES is a low count rate, photon hungry experiment!

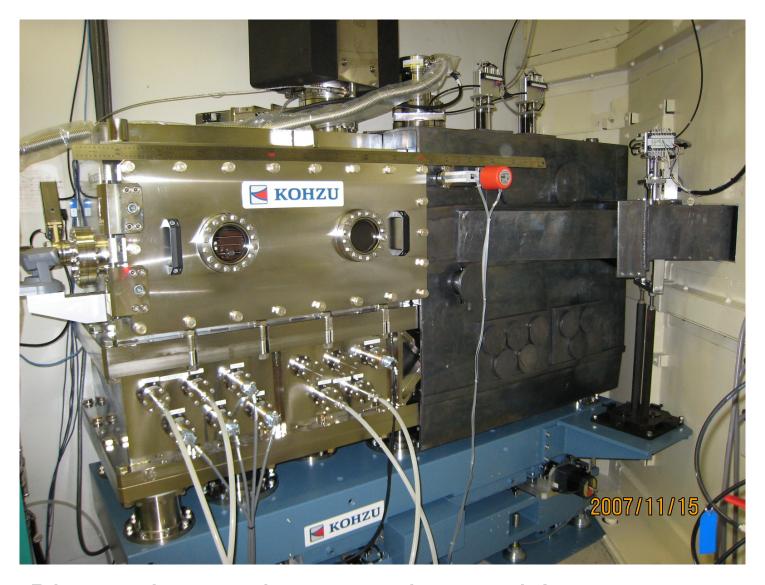
Optical design concept



HRM: vertical dispersion



Layout of the side beamline of BL12XU

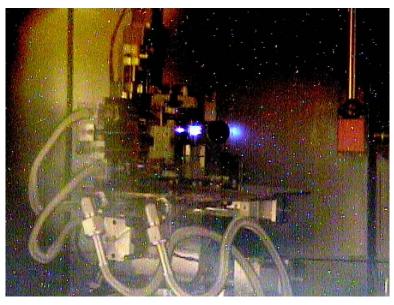


Diamond monochromator: installed Aug. 3, 2007

Diamond glows even under weak radiation at a fully opened gap 50 mm. Its shape is like a trapezoid.



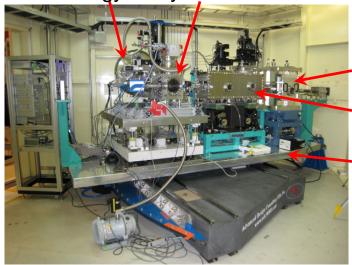
Strong radiation at a small gap 10 mm ~ 6 keV makes the diamond glow like a bright mercury-vapor lamp.
Strong scattered radiation causes snow like noise on camera.



February, 2008

Commission of SPring-8 BL12XU SL HAXPES end station – Apr. Jul. 2009

MBS energy analyzer End station



Horizontal setup

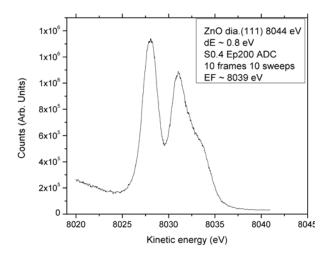
High Res. Mono. KB focus mirrors Rotational platform



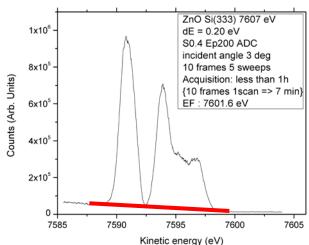
Vertical setup

KB Focus at sample Aft HRM Si(333) 7.6 keV 38x38 microns

In collaboration with Cologne U of Germany



Low resolution w/o HRM 8 keV



Medium resolution Si(333) HRM, 7.6 keV

Challenging future directions of Photoemission Spectroscopy

- ARPES at submicron to tens of nanometer scale, using Schwatzchild optics or zone plates. Need brighter light sources.
- 2. Time-resolved PES.

Pump-probe: dynamics. Need efficient detection and brighter sources.

lasers or laser+SR.

Thanks for your attention